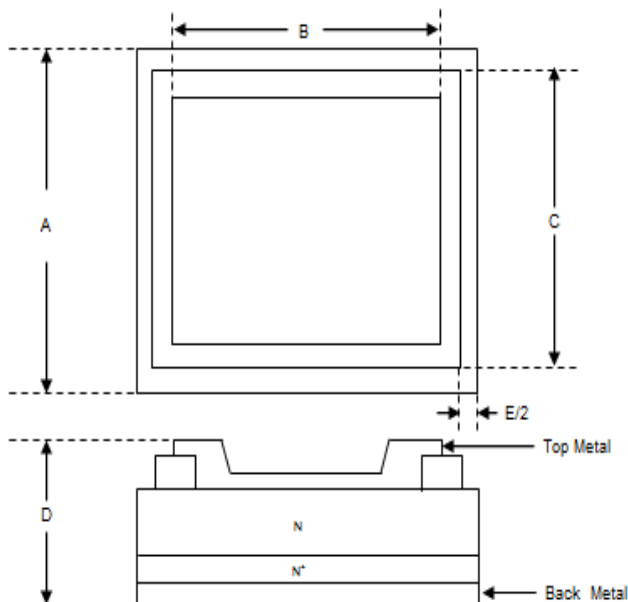


Planar Schottky Barrier Diode Wafer (PSBD)



Item	Dimensions	
	um	mil
Die Size (A)	2362	93
Top Metal Pad Size (B)	2282	89.8
Passivation Seal (C)	2302	90.6
Wafer Thickness (D)	260	10.2
Scribe Line Width (E)	60	2.36
Other Informations		
Wafer Size	6"	
Gross Die	2856	
Top Metal	Al 4um+Ag 3um	
Back Metal	Ag	

Electrical Characteristics @TA=25°C

Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.05mA	V_{RRM}	100	105	V
Maximum Average Forward Rectified Current	I_o	15	-	A
Forward Voltage Drop, @ $I_F=3A$ @ $I_F=8A$ @ $I_F=10A$ @ $I_F=15A$	V_F	- 0.84 0.85 0.9	0.7 - - -	V
Maximum Reverse Current at Rated V_{RRM}	I_R	3	1	μA
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	220	-	A
Operating Temperature Range	T_J	-50 to +175	-	°C
Storage Temperature Range	T_{STG}	-50 to +175	-	°C